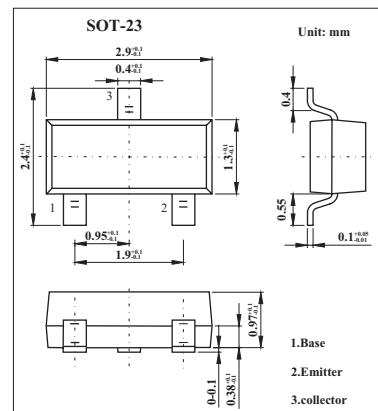


## PNP Transistor

### KC856A,B/KC857A,B,C/KC858A,B,C (BC856A,B/BC857A,B,C/BC858A,B,C)

#### ■ Features

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-80	V
KC857		-50	
KC858		-30	
Collector-Emitter Voltage	V <sub>CEO</sub>	-65	V
KC856		-45	
KC858		-30	
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current -Continuous	I <sub>C</sub>	-0.1	A
Collector Power Dissipation	P <sub>C</sub>	200	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-65 to +150	°C

**KC856A,B/KC857A,B,C/KC858A,B,C**  
**(BC856A,B/BC857A,B,C/BC858A,B,C)**

■ Electrical Characteristics  $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage KC856 KC857 KC858	V <sub>CBO</sub>	$I_c = -10\mu A, I_e = 0$	-80			V
			-50			
			-30			
Collector-emitter breakdown voltage KC856 KC857 KC858	V <sub>CEO</sub>	$I_c = -10 mA, I_b = 0$	-65			V
			-45			
			-30			
Emitter-base breakdown voltage	V <sub>EBO</sub>	$I_E = -10\mu A, I_c = 0$	-5			V
Collector cut-off current KC856 KC857 KC858	I <sub>CBO</sub>	V <sub>CB</sub> = -70 V, $I_E = 0$				$\mu A$
		V <sub>CB</sub> = -45 V, $I_E = 0$				
		V <sub>CB</sub> = -25 V, $I_E = 0$				
Collector cut-off current KC856 KC857 KC858	I <sub>CEO</sub>	V <sub>CE</sub> = -60 V, $I_B = 0$				$\mu A$
		V <sub>CE</sub> = -40 V, $I_B = 0$				
		V <sub>CE</sub> = -25 V, $I_B = 0$				
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5 V, $I_c = 0$			-0.1	$\mu A$
DC current gain KC856A, 857A, 858A KC856B, 857B, 858B KC857C, KC858C	h <sub>FE</sub>	V <sub>CE</sub> = -5V, $I_c = -2mA$	120	250		
			220	475		
			420	800		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -100mA, I_B = -5 mA$			-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = -100 mA, I_B = -5mA$			-1.1	V
Collector capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, f=1MHz			4.5	pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5 V, $I_c = -10mA, f = 100MHz$	100			MHz

■ Marking

NO.	KC856A	KC856B
Marking	3A	3B

NO.	KC857A	KC857B	KC857C
Marking	3E	3F	3G

NO.	KC858A	KC858B	KC858C
Marking	3J	3K	3L

## KC856A,B/KC857A,B,C/KC858A,B,C (BC856A,B/BC857A,B,C/BC858A,B,C)

### ■ Typical Characteristics

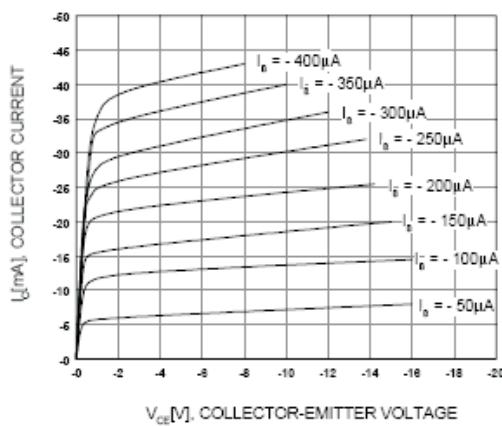


Fig.1 Static Characteristic

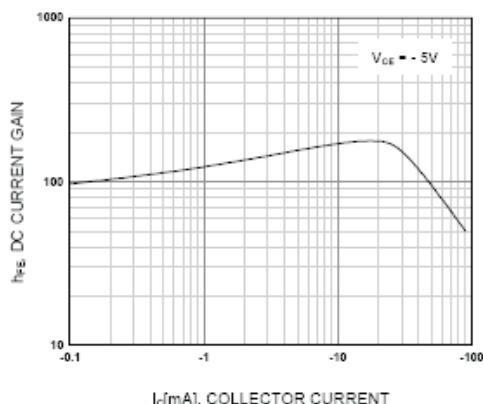


Fig.2 DC Current Gain

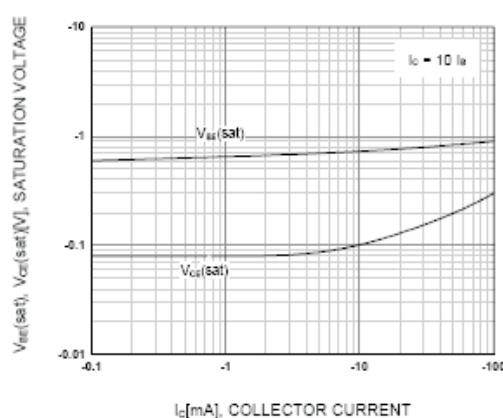
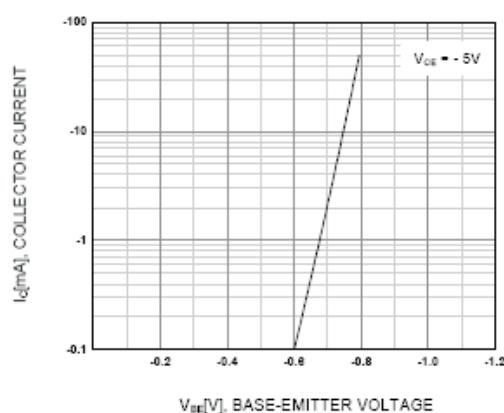
Fig.3 Base Emitter Saturation Voltage  
Collector Emitter Saturation Voltage

Fig.4 Base Emitter ON Voltage

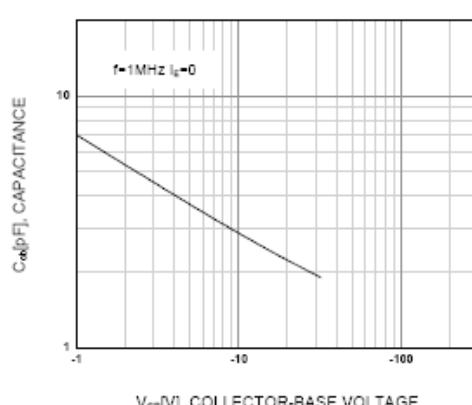


Fig.5 Collector Output Capacitance

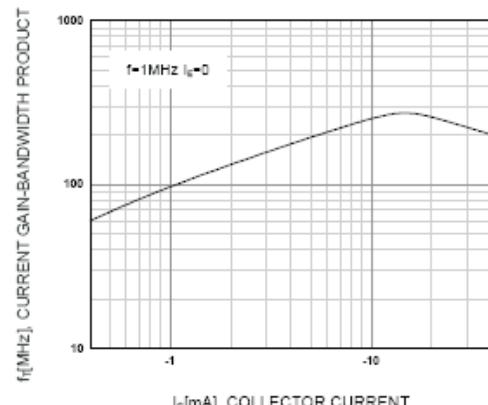


Fig.6 Current Gain Bandwidth Product

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